

### **Amendment to the Claims**

This listing of claims will replace all prior versions, and listings, of claims in the application:

#### **Listings of Claims**

Claims 1-12 (canceled)

Claim 13 (original): A chemical mechanical polishing method, comprising simultaneously removing a conductive layer, a silicon oxide layer and a silicon nitride layer using a polishing slurry comprising an abrasive, deionized water, a pH controlling agent, and polyethylene imine having a molecular structure of  $[-CH_2CH_3N(CH_2CH_2NH_2)-]_x[-CH_2CH_2NH_2-]_y$ , where x and y are 0 or positive integers.

Claim 14 (original): The method of claim 13, wherein the silicon oxide layer is one selected from the group consisting of a borophosphosilicate glass (BPSG), a phosphoresilicate glass (PSG), a borosilicate glass (BSG), a high density plasma (HDP) silicon oxide layer, an undoped silicate glass (USG), a high thermal (HT)-USG, and a plasma enhanced (PE)-silicon oxide layer.

Claim 15 (original): The method of claim 13, wherein the silicon nitride layer is a dielectric material having a basic formula of  $\text{Si}_3\text{N}_4$ .

Claim 16 (original): The method of claim 13, wherein the polyethyleneimine comprises more than 0.02 wt% of the polishing slurry.

Claim 17 (original): The method of claim 16, further comprising adding a choline derivative to the polishing slurry, wherein relative removal rates of the silicon oxide layer and the silicon nitride layer are reduced while maintaining a larger removal rate of the conductive layer, and the removal rate of the silicon oxide layer is slightly greater than the removal rate of the silicon nitride layer.

Claim 18 (original): The method of claim 17, wherein the choline derivative is choline chloride.

Claim 19 (original): The method of claim 17, wherein the choline derivative is one selected from the group consisting of choline chloride, choline base, choline bromide, choline iodide, choline dihydrogen citrate, choline bitartrate, choline bicarbonate, choline citrate, choline ascobate, choline borate, choline theophyllinate, choline gluconate, acetylcholine chloride, acetylcholine bromide, and methacholine chloride.

Claim 20 (currently amended): ~~The polishing slurry~~ The method of claim 13, wherein the polyethylene imine comprises more than 0.02 wt% of the polishing slurry, and further comprising adding a choline derivative to the polishing slurry, wherein removal rates of the silicon oxide layer and the silicon nitride layer are reduced while maintaining a larger removal rate of the conductive layer.